

SMD Type

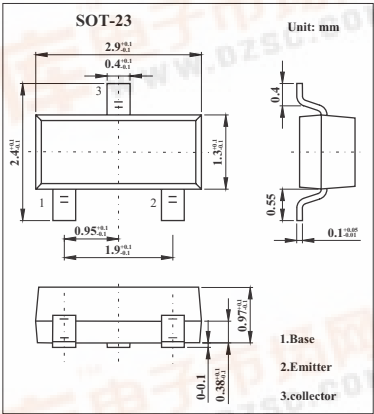
Transistors

Power High Performance Transistor

FMMT495

Features

- SOT23 NPN silicon planar medium



Absolute Maximum Ratings Ta = 25°C

Parameter	Symbol	Rating	Unit
Collector-base voltage	V _{CB0}	170	V
Collector-emitter voltage	V _{CE0}	150	V
Emitter-base voltage	V _{EB0}	5	V
Peak collector current	I _{CM}	2	A
Collector current	I _C	1	A
Base current	I _B	200	mA
Power dissipation	P _{tot}	500	mW
Operating and storage temperature range	T _j , T _{stg}	-55 to +150	°C

FMMT495

■ Electrical Characteristics Ta = 25°C

Parameter	Symbol	Testconditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V(BR)CBO	IC=100μA	170			V
Collector-emitter breakdown voltage *	V(BR)CEO	IC=10mA	150			V
Emitter-base breakdown voltage	V(BR)EBO	IE=100μA	5			V
Collector Cut-Off Currents	ICBO	VCE=150V			100	nA
Collector Cut-Off Currents	ICES	VCE=150V			100	nA
Emitter cut-off current	IEBO	VEB=4V			100	nA
Collector-emitter saturation voltage *	VCE(sat)	IC=250mA, IB=25mA IC=500mA, IB=50mA			0.2 0.3	V
Base-emitter saturation voltage *	VBE(sat)	IC=500mA, IB=50mA			1.0	V
Base-emitter voltage *	VBE(ON)	IC=500mA, VCE=10V			1.0	V
Static Forward Current Transfer Ratio	hFE	IC=1mA, VCE=10V	100			
		IC=250mA, VCE=10V*	100		300	
		IC=500mA, VCE=10V*	50			
		IC=1A, VCE=10V*	10			
Transition Frequency	fT	IC=50mA, VCE=10V, f=100MHz	100			MHz
Collector-Base Breakdown Voltage	Cobo	VCE=10V, f=1MHz			10	pF

* Pulse test: tp = 300 μs; d ≤ 0.02.

■ Marking

Marking	495
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